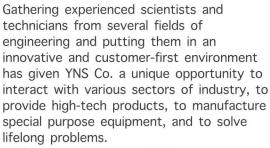
HIGH VACUUM DEPOSITION SYSTEMS



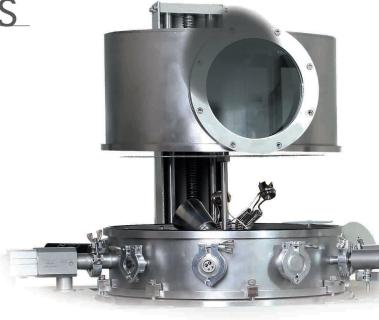


High vacuum system: Equipment to create low pressure condition 10-8 torr for special operations.

Coating system: Equipment for deposition

thin film materials

(Insulator/Conductor/Superconductor)



COATING SYSTEMS

YNS coating systems can be configured with a wide range of accessories for evaporation and sputtering or can be combined together to provide a flexible multi-process deposition system. Systems are designed and customized from a range of deposition sources, chamber sizes, and 19 inch rack cabinets to suit individual requirements.

Deposition techniques available:

- DC magnetron sputtering
- RF magnetron sputtering
- · Resistive thermal evaporation

J Applications

- Anti-reflective coatings
- Semiconductors
- Mirrors
- · Compact disc master metallization
- Dielectrics
- Organics, polymers and OLEDs
- Photonics research
- Solar cells
- Nanotechnology

Technical Specifications

Ultimate pressure	1×10 ⁻⁶ torr	
Chamber	304 stainless steel chamber- Integral hoists for chamber bell jar	
Ports	Eight radial process ports	
Pumps	Standard Diffusion and cold trap pumping. Pumpdown times are automatically kept to a minimum.	
Substrate size and temperature	Accommodates substrates up to 300mm - Substrate heating to 200° C	
Sputtering source	Two magnetron sputtering sources	
Film thickness monitoring	Film thickness monitoring with quartz crystal holder	
Valves	high vacuum valve (pneumatic butterfly valve), on/off valve, needle valve, purge valve	
Sputtering Power	DC power supply: 800 V - 1 A	
Supplies	RF power supply: Frequency 13.86 MHz - 230 watt	
Thermal evaporation power supplies	100 amperes with 10 volts	

PECVD-RIE system

This is a dual-chamber system. This system can be used for various research and industrial application. Plasma-enhanced chemical vapor deposition (PECVD) is a process used to deposit thin films from a gas state (vapor) on the different substrates. It used for the deposition of dielectric and passivation films such as silicon oxide or silicon nitride .

Reactive-lon Etching (RIE) is one of the methods for dry etching and used in semiconductor and superconductor devices fabrication. RIE is the combination of chemical and physical etching. This system is a simplified modification for etching semiconductors, dielectric and metal layers in capacitive discharge plasma.



Technical Specification

16.		
Vacuum chamber	2 Cylindrical Vacuum chamber: diameter 10 inch (250mm) and length 200mm and 100mm	
Vacuum pumping	Turbo pump with dual stage rotary as backing pump	
Base pressure	1×10 ⁻⁶ torr	
RF Generator	RF Generator and Automatch (AMU) with power 200w	
Mass Flow Controller	4 MFC-controlled gas lines and needle valves	
Maximum substrate	Maximum substrate temperatures (typ. 450° C) for PECVD	
temperatures		
System control	PLC (Programmable Logic Controller)	
Capabilities	Deposition and etching of thin films	
Electrodes	Top electrode with high uniformity shower head	
Etch rate	Depends on the gases and materials- adjustable	
Max substrate	Max substrate diameter 3 inch	
diameter		



Sputter coater & thermal evaporation

Deposition Methods	Sputtering and thermal evaporating
Vacuum chamber	Cylindrical glass chamber Diameter : 300mm, Height: 200 mm
Thinkness measurment system	Thickness measurment of deposited layers and rate of deposition with crystal Quartz
Magnetron sputtering Source	800 W
Evaporation source	150 amper
Max substrate size	5 inches
Base pressure	1×10 ⁻³ torr

This desktop coating system is a suitable unit for SEM & TEM sample preparation.



Steel Vacuum Chamber

- Vacuum range 1×10⁻⁸ torr
 Finish: Glassbead blast standard
- Materials Flanges and body: 304 SS/O-rings: Viton & NBR
 Multi flange ISO-KF and ISO-K port
- connection
- Glass viewports



Glass vacuum belljar

- Made from pyrex to withstand thermal shock and chemical attack
- Available in various diameters and lengths
- Features good high-vacuum properties



Diffusion pump DP100, DP150

- Max pressure: ×10⁻⁷ torr
 Speed: 250, 700 L/S



- Liquid nitrogen cold trap
 Designed to reach ×10⁻⁸ torr
 Design to reduce backstreaming
- Flange size: Standard DN100



- High Current Electrodes
 Standard 1" diameter baseplate mounting
 • 100 A, 50 V Max
- Water cooled
- Vacuum Range: 1×10⁻⁷ torr



Rotary Feedthrough

- · Rotary motion with magnetic and direct coupling

 • Vacuum Range: 1×10⁻⁸ torr

 • Standard 1" diameter baseplate
- mounting



- Active Vacuum Pirani gauge
 Measurement range: 1×10⁻³ torr
 Vacuum range: 1×10⁻⁷torr
 Flange size: Standard DN10



Gauge Display

- · Compatible with pirani and cold cathode gauge
- Electrical connection: RJ45
- Temperature storage: 0-30 °c



- Cold Cathode Ionization Gauge
 Measurement range: 1×10⁻³-1×10⁻⁶torr
 Vacuum range: 1×10⁻⁷ torr
 Flange size: Standard DN25



- Butterfly valve
 Vacuum range: 1×10⁻⁶torr
- Materials Flanges and body: 304 SS/O-rings NBR
 Flange Size: ISO-KF, ISO-K



Vacuum Connection and Flanges

- HV rated to ×10⁻⁸torr High temperature rated to 150 °C
- ISO compatible design304 Stainless Steel
- · Elastomer O-ring seal: NBR or Viton



- Needle valve and Plug valve
 Vacuum Range: 1×10⁻⁶torr,
 1×10⁻⁸torr
- Two DN10 ports

